

In the Specification:

Please replace the paragraph beginning on page 7 line 23 with the following amended paragraph:

Figures 2 and 5 illustrate the programming of a zero bit in a cell of an EPROM according to a second embodiment of the present invention, in which the storage method parameter is the target threshold voltage. Programming voltage pulse train 12 of Figure 2 is applied to the cell, as in the prior art, but only until the threshold voltage reaches a target value that is sufficiently close to a voltage V_0' that is less than V_0 . Because V_0' is less than V_0 , the cell of Figure 5 is programmed in less time than the cell of Figures 1 and 2, at the expense of the distribution 30 of the resulting floating gate voltages being closer to V_T than distribution 16, which is shown in Figure [[2]] 5 in phantom for reference. It follows that the lower end 32 of distribution 30 drifts down to V_T sooner than lower end 18 of distribution 16; but if it takes much longer than *e.g.* one month for lower end 32 to drift down to V_T , this embodiment of the present invention is suitable for storing data, such as “cached” Web pages, that need to be archived for only one month. Data that need to be archived for many years are programmed as illustrated in Figure 1.